



Correction: Tunnel injection from WS₂ quantum dots to InGaN/GaN quantum wells

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 Correction for 'Tunnel injection from WS₂ quantum dots to InGaN/GaN quantum wells' by Svette Reina Merden Santiago *et al.*, *RSC Adv.*, 2018, 8, 15399–15404.

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Eqn (4) in the published paper was incorrect; the correct version is shown below:

$$\tau_T \propto \exp \left[2L \sqrt{(2m^*/\hbar^2)(V - E)} \right] \quad (4)$$

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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